

## INCHANGE SEMICONDUCTOR

# **isc Silicon NPN Power Transistor**

# 2SD2559

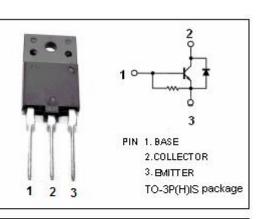
### DESCRIPTION

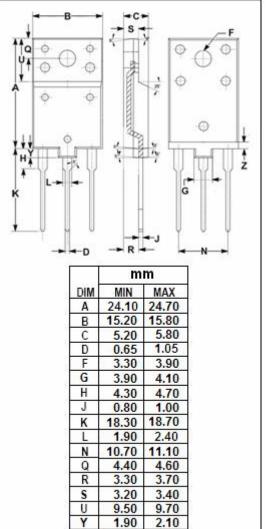
- · High Breakdown Voltage-
  - : V<sub>CBO</sub>= 1500V (Min)
- · High Switching Speed
- · Low Saturation Voltage
- Built-in Damper Diode
- · Minimum Lot-to-Lot variations for robust device performance and reliable operation

## **APPLICATIONS**

• Designed for color TV horizontal deflection applications.

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)							
SYMBOL	PARAMETER	VALUE	UNIT				
V <sub>CBO</sub>	Collector-Base Voltage	1500	V				
V <sub>CEO</sub>	Collector-Emitter Voltage	600	V				
V <sub>EBO</sub>	Emitter-Base Voltage	5	V				
lc	Collector Current- Continuous	8	A				
I <sub>CM</sub>	Collector Current- Pulse	16	A				
I <sub>B</sub>	Base Current- Continuous	4	A				
Pc	Collector Power Dissipation @ Tc=25℃	50	W				
TJ	Junction Temperature	150	°C				
T <sub>stg</sub>	Storage Temperature Range	-55~150	Ĉ				





## isc website: www.iscsemi.com

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1.40

1.60



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## ELECTRICAL CHARACTERISTICS

#### $T_{c}\text{=}25^{\circ}\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 200mA ; I <sub>C</sub> = 0	5			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 6A; I <sub>B</sub> = 1.2A			5.0	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> = 6A; I <sub>B</sub> = 1.2A			1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 1500V; I <sub>E</sub> = 0			1.0	mA
Іево	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0	83		250	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V	10		30	
h <sub>FE-2</sub>	DC Current Gain	Ic= 6A; Vce= 5V	5		9	
V <sub>ECF</sub>	C-E Diode Forward Voltage	I <sub>F</sub> = 6A			1.8	V
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.1A; V <sub>CE</sub> = 10V		2		MHz
Сов	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V; f <sub>test</sub> =1.0MHz		125		pF

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